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May 2014

# FDA33N25

## N-Channel UniFET™ MOSFET

250 V, 33 A, 94 mΩ

### Features

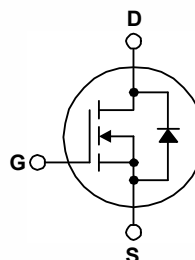
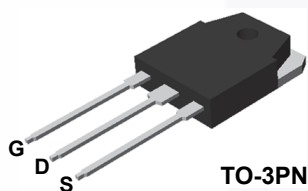
- $R_{DS(on)} = 88 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 16.5 \text{ A}$
- Low Gate Charge (Typ. 36 nC)
- Low  $C_{rss}$  (Typ. 35 pF)
- 100% Avalanche Tested
- RoHS Compliant

### Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FDA33N25	Unit
$V_{DSS}$	Drain to Source Voltage		250	V
$V_{GSS}$	Gate to Source Voltage		$\pm 30$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	33	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	21	
$I_{DM}$	Drain Current	- Pulsed (Note 1)	132	A
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	918	mJ
$I_{AR}$	Avalanche Current	(Note 1)	33	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	24.6	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	4.5	V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	245	W
		- Derate Above $25^\circ\text{C}$	1.96	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FDA33N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.51	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA33N25	FDA33N25	TO-3PN	Tube	N/A	N/A	30 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$ , $T_J = 25^\circ\text{C}$	250	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.34	-	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 250\ \text{V}$ , $V_{GS} = 0\ \text{V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 200\ \text{V}$ , $T_C = 125^\circ\text{C}$	-	-	10	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\ \text{V}$ , $V_{DS} = 0\ \text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 16.5\ \text{A}$	-	0.088	0.094	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\ \text{V}$ , $I_D = 16.5\ \text{A}$	-	24.2	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	-	1655	2200	pF
$C_{oss}$	Output Capacitance		-	315	420	pF
$C_{rss}$	Reverse Transfer Capacitance		-	35	55	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 200\ \text{V}$ , $I_D = 33\ \text{A}$ , $V_{GS} = 10\ \text{V}$ (Note 4)	-	36	46.8	nC
$Q_{gs}$	Gate to Source Gate Charge		-	10.8	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	16	-	nC

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\ \text{V}$ , $I_D = 33\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_G = 25\ \Omega$ (Note 4)	-	33	76	ns
$t_r$	Turn-On Rise Time		-	142	293	ns
$t_{d(off)}$	Turn-Off Delay Time		-	77	165	ns
$t_f$	Turn-Off Fall Time		-	68	146	ns

### Drain-Source Diode Characteristics

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	33	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	132	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 33 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 33 A, dI <sub>F</sub> /dt = 100 A/μs	-	256	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	2.3	-	μC

#### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 1.35\ \text{mH}$ ,  $I_{AS} = 33\ \text{A}$ ,  $V_{DD} = 50\ \text{V}$ ,  $R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 33\ \text{A}$ ,  $di/dt \leq 200\ \text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical Characteristics

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

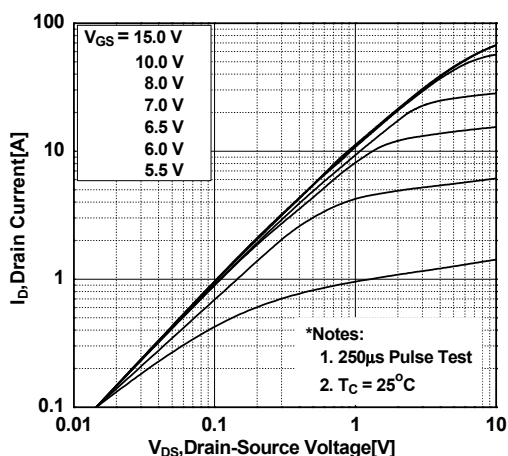


Figure 2. Transfer Characteristics

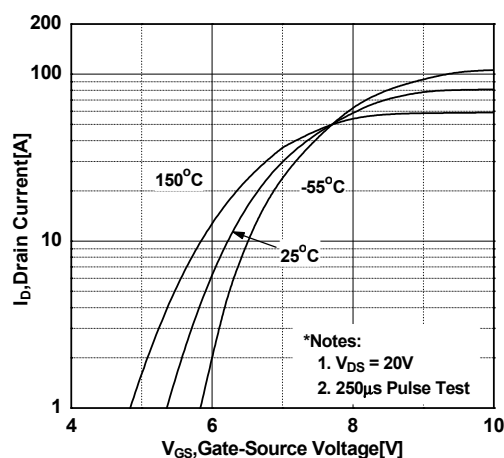


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

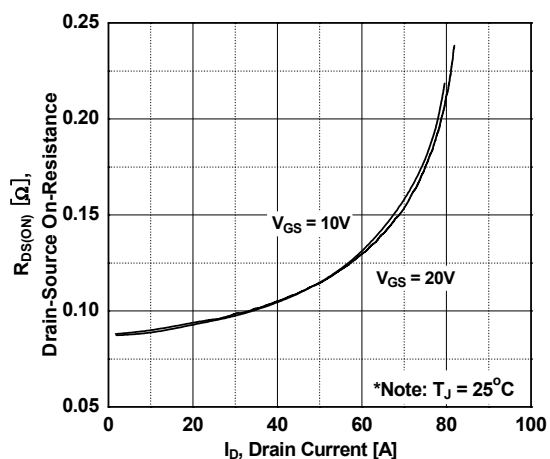


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

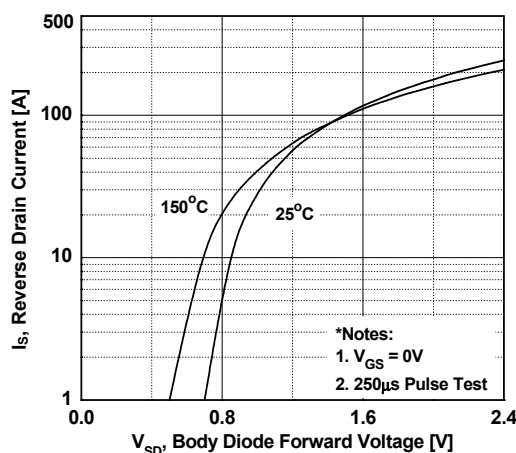


Figure 5. Capacitance Characteristics

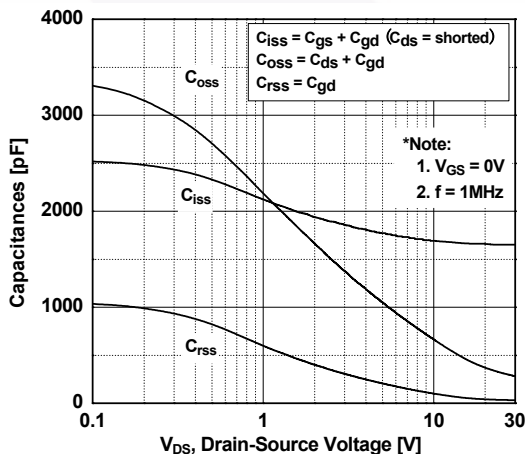
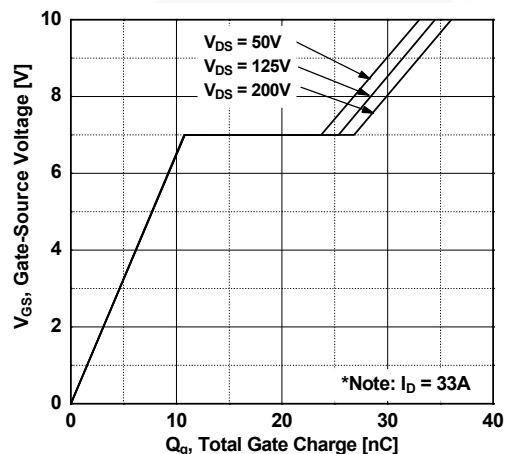


Figure 6. Gate Charge Characteristics



# Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

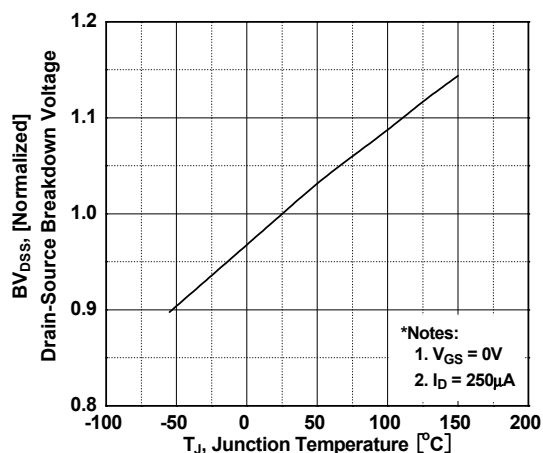


Figure 8. On-Resistance Variation vs. Temperature

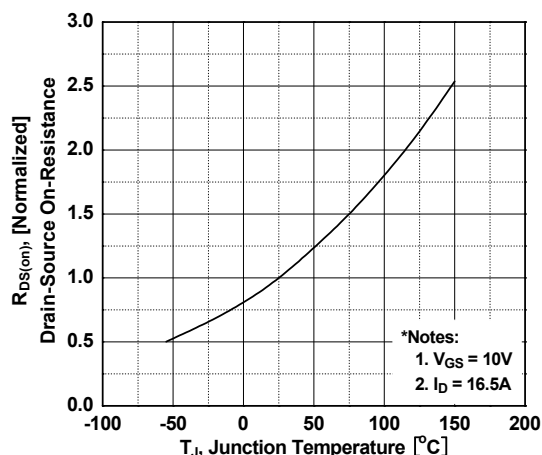


Figure 9. Maximum Safe Operating Area

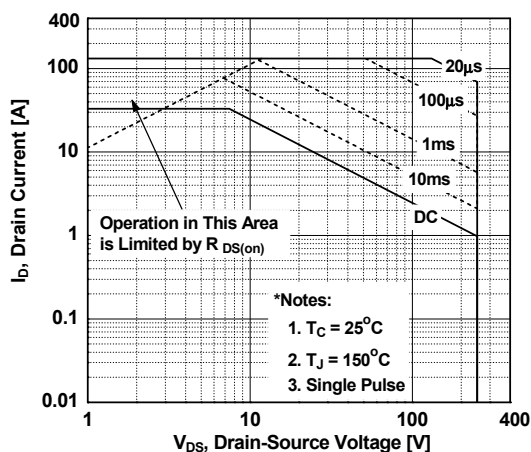


Figure 10. Maximum Drain Current vs. Case Temperature

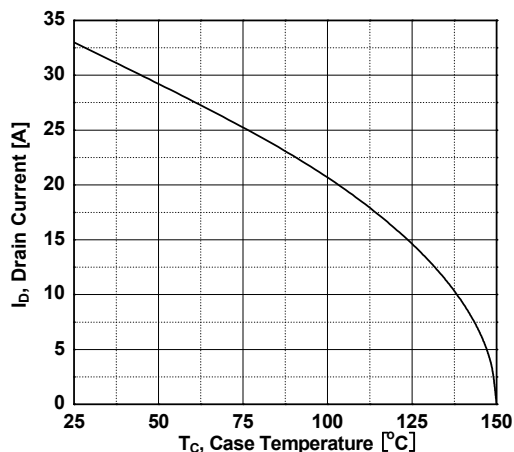


Figure 11. Transient Thermal Response Curve

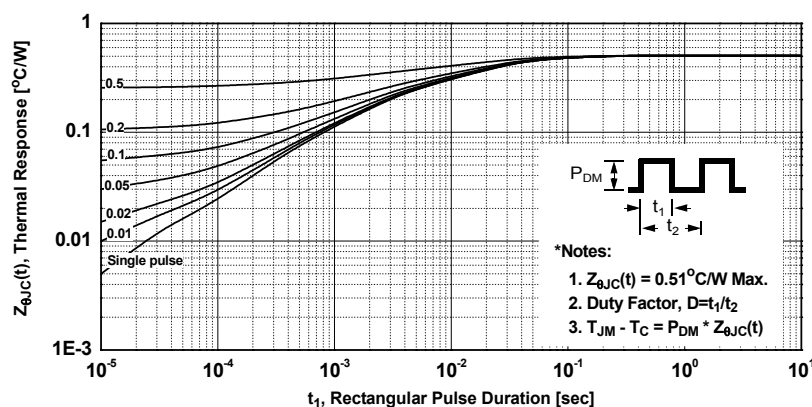




Figure 12. Gate Charge Test Circuit & Waveform

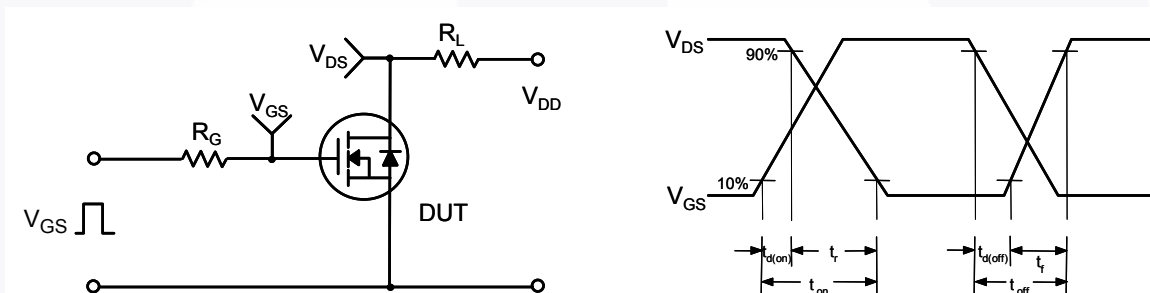


Figure 13. Resistive Switching Test Circuit & Waveforms

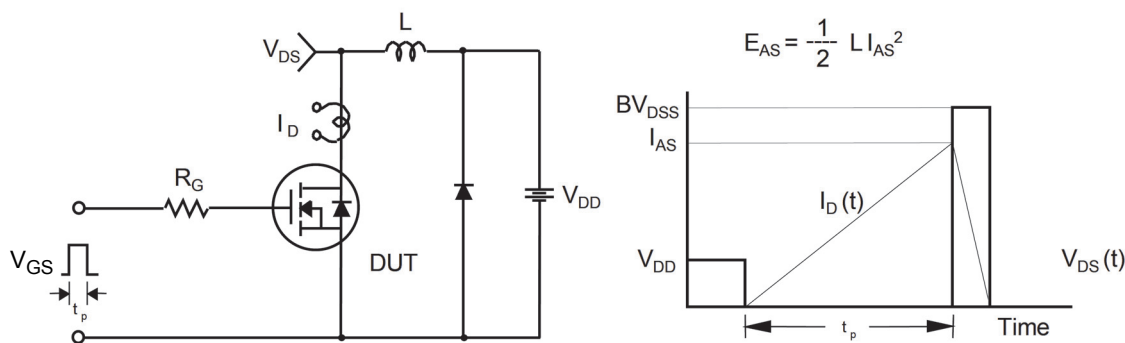
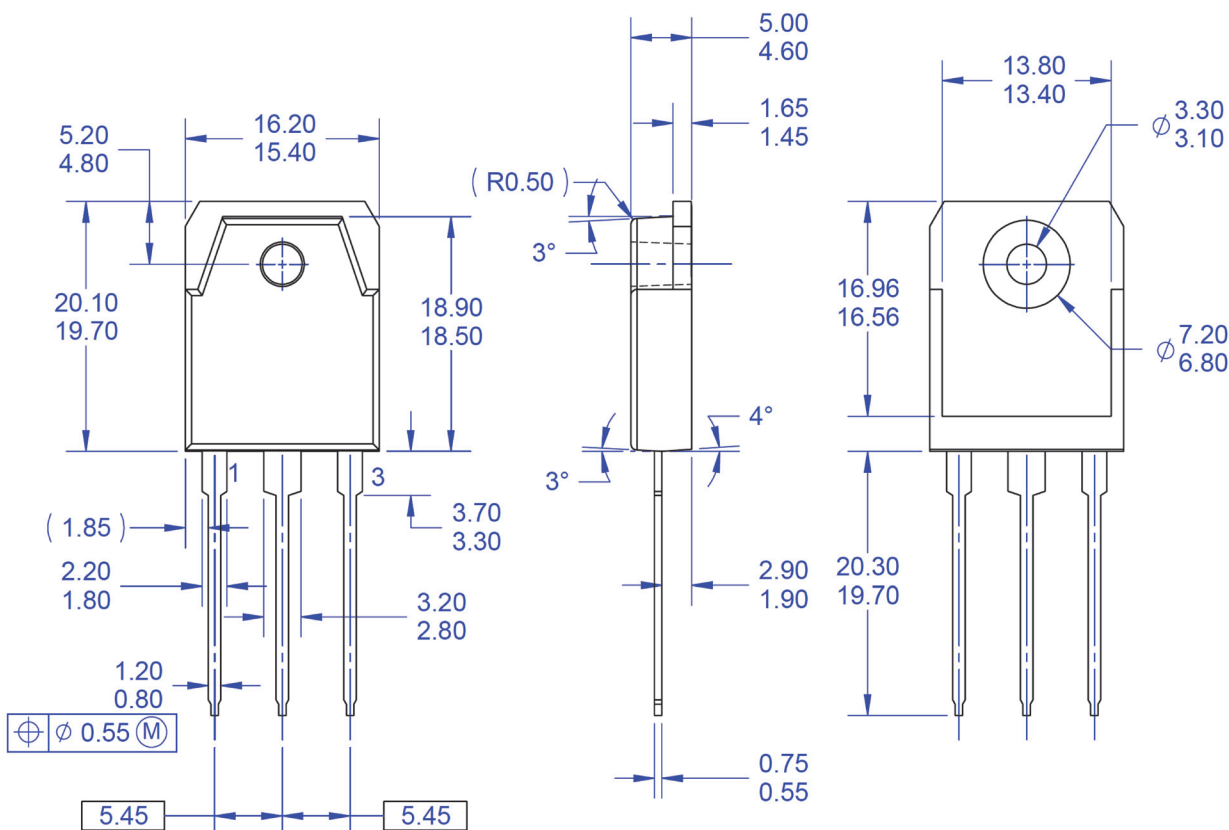


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

# Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
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- E) DRAWING FILE NAME: TO3PN03AREV1.
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**Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65**

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